

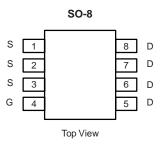
## 613SPV-VB Datasheet P-Channel 60 V (D-S) MOSFET

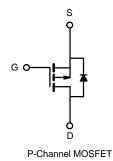
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-60			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = -10 V	0.060			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = -4.5 V	0.063			
I <sub>D</sub> (A) per leg	-8			

### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- 100 %  $R_g$  and UIS tested







<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	-60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	-8		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-4.75		
Continuous Source Current (Diode Conduction	I <sub>S</sub>	-4.5	А		
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-32		
Single Pulse Avalanche Current	1 0.1 ml	I <sub>AS</sub>	-22.4		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	25	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	5	W	
	T <sub>C</sub> = 125 °C		1.67	٧V	
Operating Junction and Storage Temperature Range		TJ, T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	110	°C/W		
Junction-to-Foot (Drain)		R <sub>thJF</sub>	30	0,00		

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	-	-			•		•
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = -250 \mu A$		-60	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$			-2.5	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -60 V	-	-	-1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V},  \text{T}_{\text{J}} = 125 ^{\circ}\text{C}$	-	-	-50	
		$V_{GS} = 0 V$	$V_{DS}$ = -60 V, $T_J$ = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -10 V$	$V_{DS} \le -5 V$	-30	-	-	А
		$V_{GS} = -10 V$	I <sub>D</sub> = -4.3 A	-	0.060	-	Ω
Drain Source On State Desistence a	<b>P</b>	$V_{GS} = -10 V$	$I_D$ = -4.3 A, $T_J$ = 125 °C	-	0.070	-	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}$	$I_D = -4.3 \text{ A}, \text{ T}_J = 175 \ ^\circ\text{C}$	-	0.080	-	
		$V_{GS} = -4.5 V$	I <sub>D</sub> = -3.8 A	-	0.063	-	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -4.3 A		-	13	-	S
Dynamic <sup>b</sup>		-					
Input Capacitance	C <sub>iss</sub>		= 0 V V <sub>DS</sub> = -30 V, f = 1 MHz	-	1500	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	334	417	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	114	142	
Total Gate Charge <sup>c</sup>	Qg			-	43.4	65	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -30 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	4.7	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	9	-	1
Gate Resistance	Rg	f = 1 MHz		1.3	2.5	4	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	17	
Rise Time <sup>c</sup>	tr	$V_{DD}$ = -30 V, R <sub>L</sub> = 8.8 $\Omega$ I <sub>D</sub> $\cong$ -5 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 $\Omega$		-	11	17	- ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	35	52	
	t <sub>f</sub>			-	6	9	
Fall Time <sup>c</sup>							
Fall Time <sup>c</sup> Source-Drain Diode Ratings and Chara							
				-	-	-32	А

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

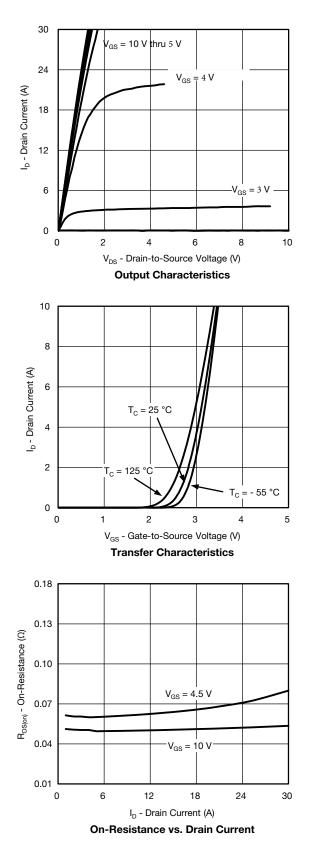
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

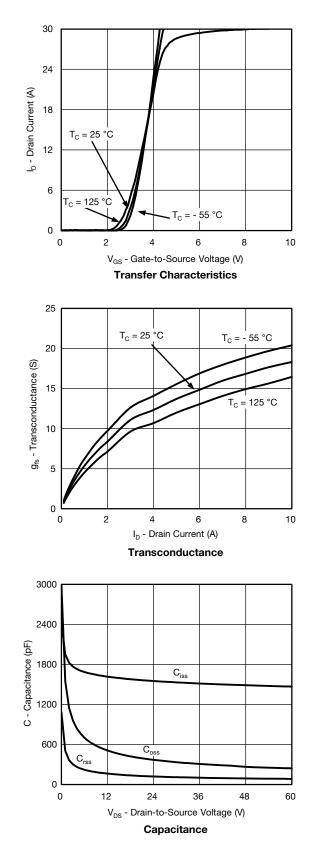
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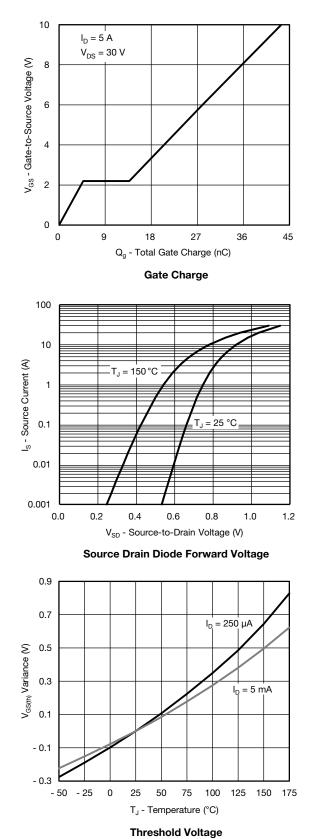
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

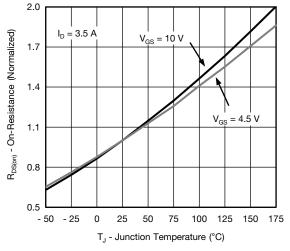




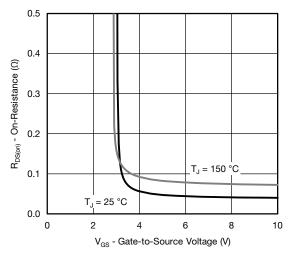


### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

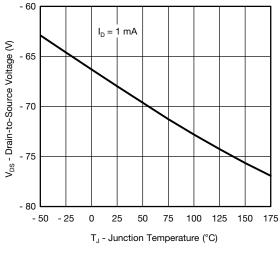




**On-Resistance vs. Junction Temperature** 



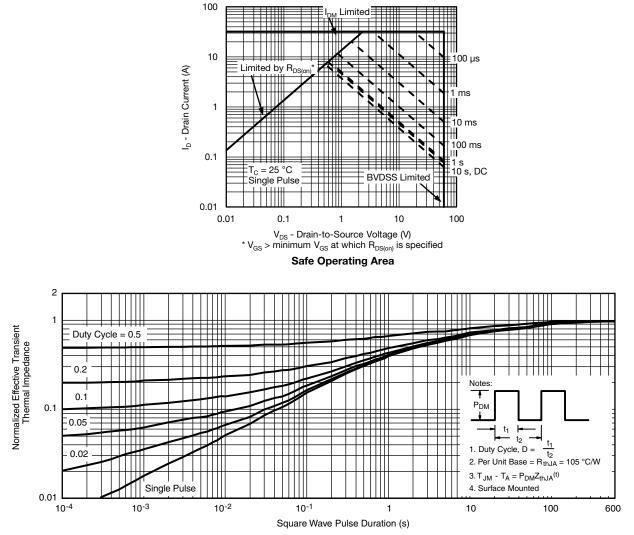
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



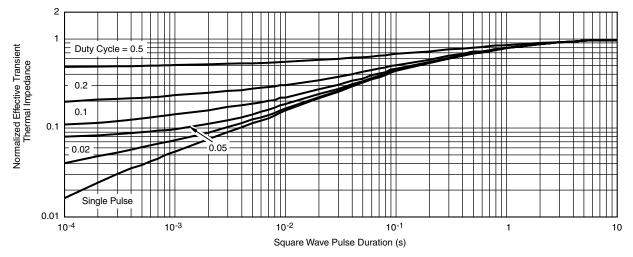
#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

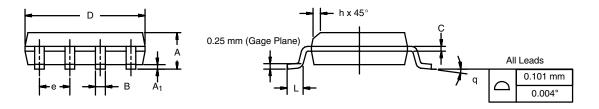
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

<sup>•</sup> The characteristics shown in the two graphs



# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012

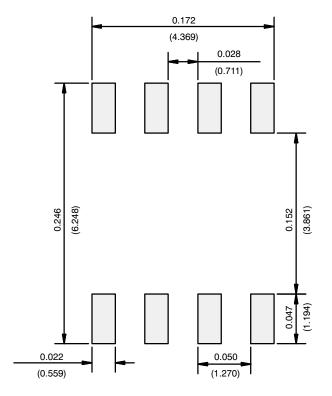




	MILLIM	ETERS	INCHES		
DIM	Min	Мах	Min	Max	
А	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)



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